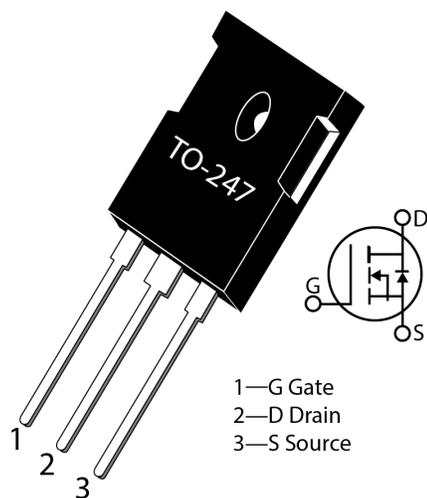


MSC090SMA070B Silicon Carbide N-Channel Power MOSFET

1 Product Overview

The silicon carbide (SiC) power MOSFET product line from Microsemi increases the performance over silicon MOSFET and silicon IGBT solutions while lowering the total cost of ownership for high-voltage applications. The MSC090SMA070B device is a 700 V, 90 mΩ SiC MOSFET in a TO-247 package.



1.1 Features

The following are key features of the MSC090SMA070B device:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{j(max)} = 175\text{ °C}$
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

1.2 Benefits

The following are benefits of the MSC090SMA070B device:

- High efficiency to enable lighter, more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

1.3 Applications

The MSC090SMA070B device is designed for the following applications:

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- H/EV powertrain and EV charger
- Power supply and distribution

2 Device Specifications

This section shows the specifications for the MSC090SMA070B device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the MSC090SMA070B device.

Table 1 • Absolute Maximum Ratings

Symbol	Characteristic	Ratings	Unit
V _{DSS}	Drain source voltage	700	V
I _D	Continuous drain current at T _c = 25 °C	28	A
	Continuous drain current at T _c = 100 °C	20	
I _{DM}	Pulsed drain current ¹	69	
V _{GS}	Gate-source voltage	23 to -10	V
P _D	Total power dissipation at T _c = 25 °C	90	W
	Linear derating factor	0.60	W/°C

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

The following table shows the thermal and mechanical characteristics for the MSC090SMA070B device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R _{θJC}	Junction-to-case thermal resistance		1.0	1.5	°C/W
T _J	Operating junction temperature	-55		175	°C
T _{STG}	Storage temperature	-55		150	
T _L	Soldering temperature for 10 seconds (1.6 mm from case)			260	
				10	lbf-in
				1.1	N-m
Wt	Package weight		0.22		oz
			6.2		g

2.2 Electrical Performance

The following table shows the static characteristics for the MSC090SMA070B device. $T_J = 25^\circ\text{C}$ unless otherwise specified.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	700			V
$R_{DS(on)}$	Drain-source on resistance ¹	$V_{GS} = 20\text{ V}, I_D = 15\text{ A}$		86	108	m Ω
$V_{GS(th)}$	Gate-source threshold voltage	$V_{GS} = V_{DS}, I_D = 0.75\text{ mA}$	1.9	2.4		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold voltage coefficient	$V_{GS} = V_{DS}, I_D = 0.75\text{ mA}$		-3.4		mV/ $^\circ\text{C}$
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 700\text{ V}, V_{GS} = 0\text{ V}$			100	μA
		$V_{DS} = 700\text{ V}, V_{GS} = 0\text{ V}$ $T_J = 125^\circ\text{C}$			500	
I_{GSS}	Gate-source leakage current	$V_{GS} = 20\text{ V}/-10\text{ V}$			± 100	nA

Notes:

1. Pulse test: pulse width < 380 μs , duty cycle < 2%.

The following table shows the dynamic characteristics for the MSC090SMA070B device. $T_J = 25^\circ\text{C}$ unless otherwise specified.

Table 4 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}, V_{DD} = 700\text{ V}, V_{AC} = 25\text{ mV},$ $f = 1\text{ MHz}$		785		pF
C_{rss}	Reverse transfer capacitance			5		
C_{oss}	Output capacitance			85		
Q_g	Total gate charge	$V_{GS} = -5\text{ V}/20\text{ V}, V_{DD} = 470\text{ V}$ $I_D = 15\text{ A}$		38		nC
Q_{gs}	Gate-source charge			10		
Q_{gd}	Gate-drain charge			6		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 470\text{ V}, V_{GS} = -5\text{ V}/20\text{ V}, I_D = 15\text{ A}$ $R_{G(ext)} = 4\ \Omega$ ¹		20		ns
t_r	Current rise time	Freewheeling diode =		9		
$t_{d(off)}$	Turn-off delay time			31		
t_f	Current fall time	MSC090SMA070B ($V_{GS} = -5\text{ V}$)		10		
E_{on}	Turn-on switching energy ²			85		μJ
E_{off}	Turn-off switching energy			14		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 470\text{ V}, V_{GS} = -5\text{ V}/20\text{ V}, I_D = 15\text{ A}$ $R_{G(ext)} = 4\ \Omega$ ¹		20		ns
t_r	Current rise time	Freewheeling diode = MSC010SDA070B		7		
$t_{d(off)}$	Turn-off delay time			30		
t_f	Current fall time			7		
E_{on}	Turn-on switching energy ²			67		μJ
E_{off}	Turn-off switching energy			14		
ESR	Equivalent series resistance	$f = 1\text{ MHz}, 25\text{ mV},$ drain short		4		Ω
SCWT	Short circuit withstand time	$V_{DS} = 560\text{ V}, V_{GS} = 20\text{ V}$		3		μs

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
E_{AS}	Avalanche energy, single pulse	$V_{DS} = 150\text{ V}$, $V_{GS} = 20\text{ V}$, $I_D = 15\text{ A}$		770		mJ

Notes:

1. R_G is total gate resistance excluding internal gate driver impedance.
2. E_{on} includes energy of freewheeling diode.

The following table shows the body diode characteristics for the MSC090SMA070B device. $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Table 5 • Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$I_{SD} = 15\text{ A}$, $V_{GS} = 0\text{ V}$		4.0		V
		$I_{SD} = 15\text{ A}$, $V_{GS} = -5\text{ V}$		4.2		V
t_{rr}	Reverse recovery time	$I_{SD} = 15\text{ A}$, $V_{GS} = -5\text{ V}$		24		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 470\text{ V}$ $di/dt = -1200\text{ A}/\mu\text{s}$		134		nC
I_{RRM}	Reverse recovery current			9		A

2.3 Typical Performance Curves

This section shows the typical performance curves for the MSC090SMA070B device.

Figure 1 • Drain Current vs. Drain-to-Source Voltage

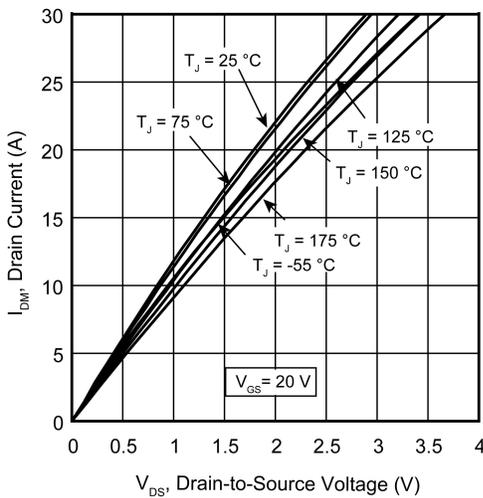


Figure 2 • Drain Current vs. Drain-to-Source Voltage

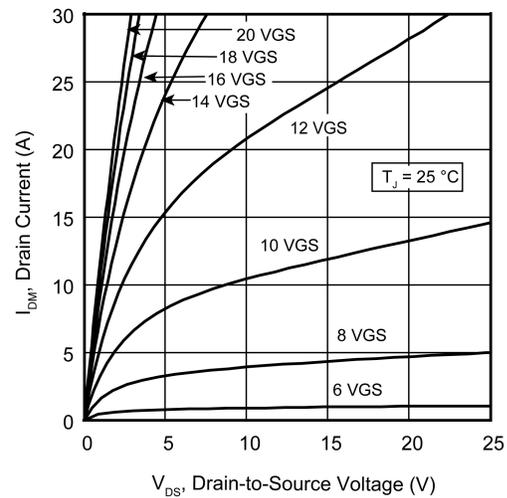


Figure 3 • Drain Current vs. Drain-to-Source Voltage

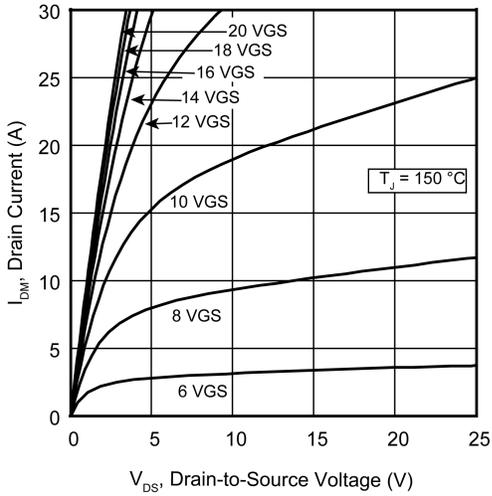


Figure 4 • Drain Current vs. Drain-to-Source Voltage

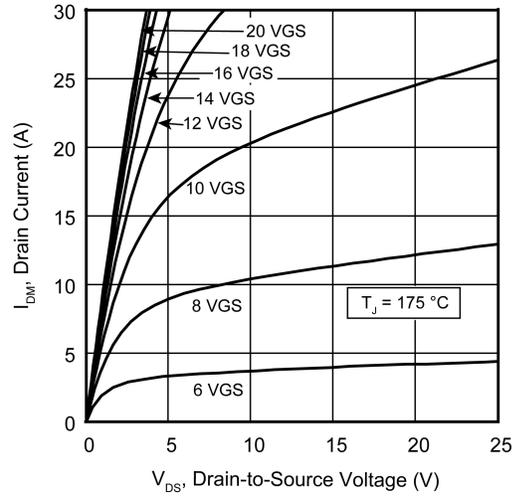


Figure 5 • RDS(on) vs. Junction Temperature

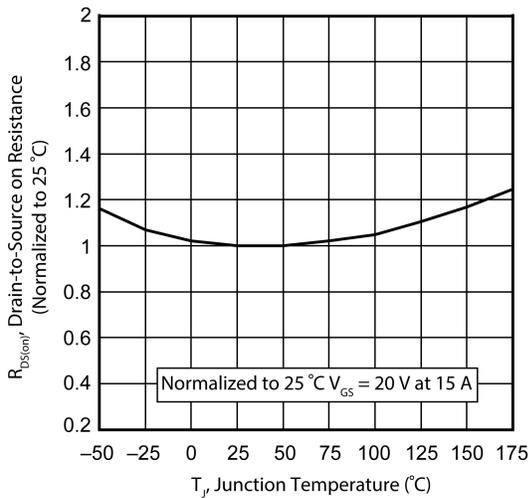


Figure 6 • Gate Charge Characteristics

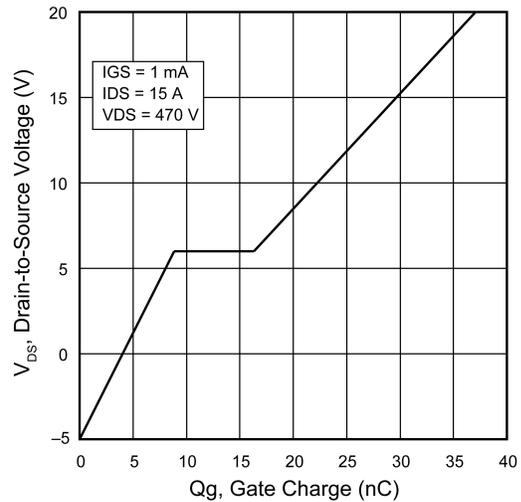


Figure 7 • Capacitance vs. Drain-to-Source Voltage

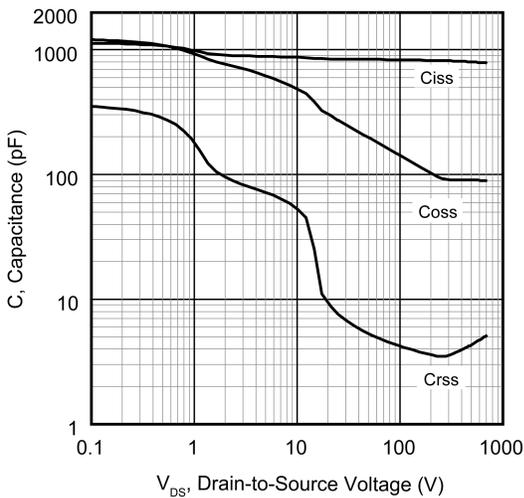


Figure 8 • IDM vs. Gate-to-Source Voltage

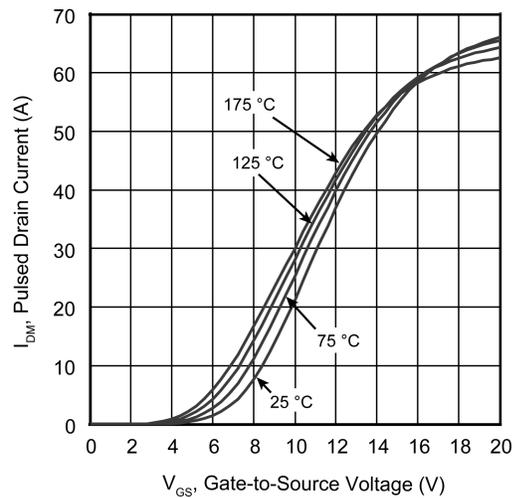


Figure 9 • IDM vs. VDS Third Quadrant Conduction

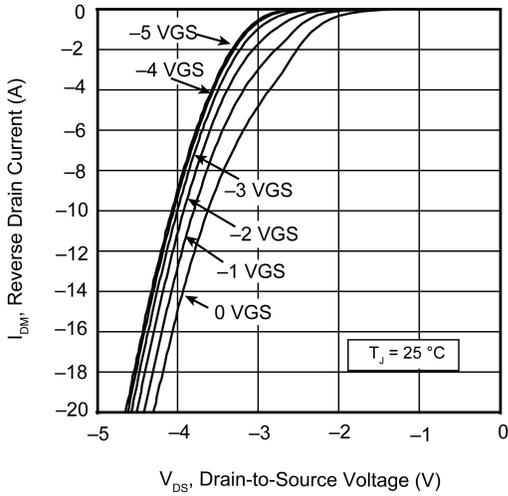


Figure 10 • IDM vs. VDS Third Quadrant Conduction

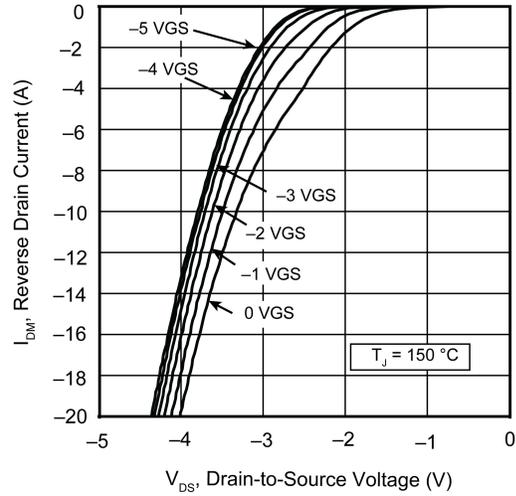


Figure 11 • VGS(th) vs. Junction Temp.

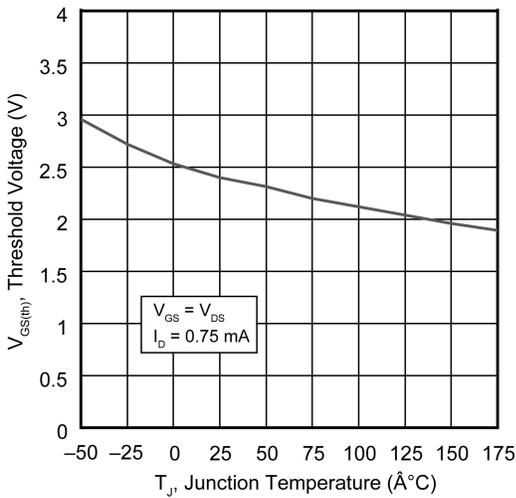


Figure 12 • Forward Safe Operating Area

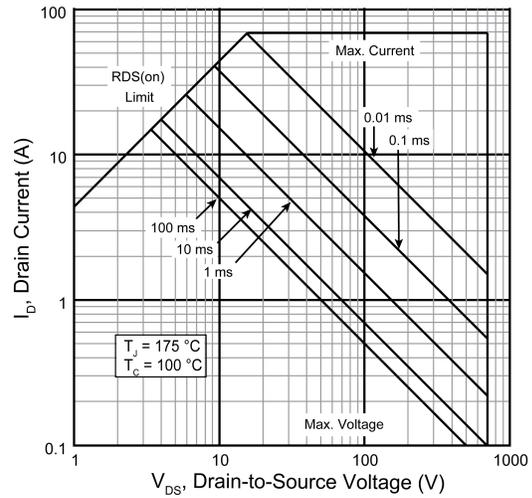
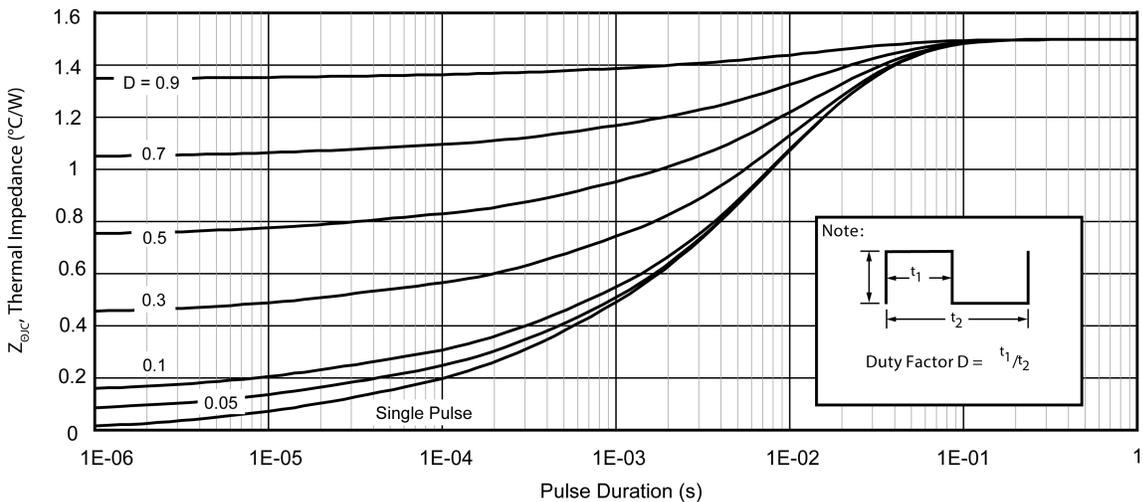


Figure 13 • Maximum Transient Thermal Impedance



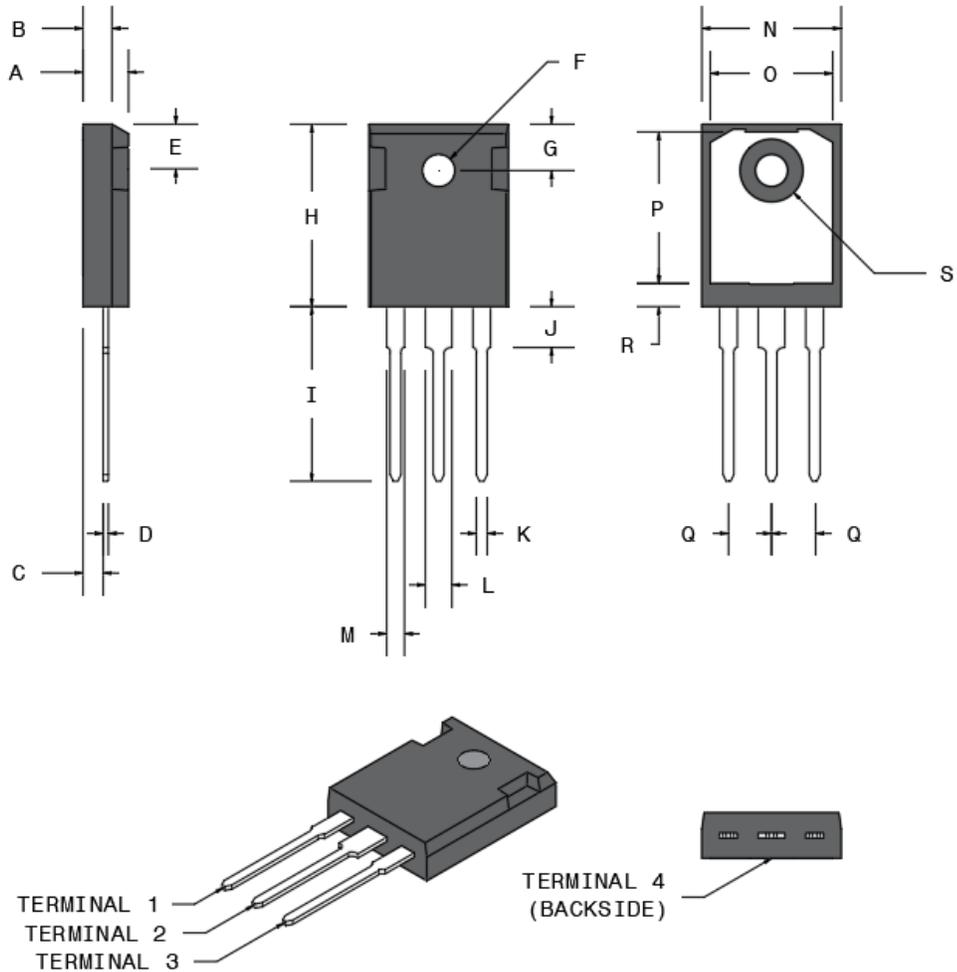
3 Package Specification

This section shows the package specification for the MSC090SMA070B device.

3.1 Package Outline Drawing

The following figure illustrates the TO-247 package drawing for the MSC090SMA070B device. The dimensions in the figure below are in millimeters and (inches).

Figure 14 • Package Outline Drawing



The following table shows the MSC090SMA070B dimensions and should be used in conjunction with the package outline drawing.

Table 6 • TO-247 Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
A	4.69	5.31	0.185	0.209
B	1.49	2.49	0.059	0.098
C	2.21	2.59	0.087	0.102
D	0.40	0.79	0.016	0.031
E	5.38	6.20	0.212	0.244
F	3.50	3.81	0.138	0.150
G	6.15 BSC		0.242 BSC	
H	20.80	21.46	0.819	0.845
I	19.81	20.32	0.780	0.800
J	4.00	4.50	0.157	0.177
K	1.01	1.40	0.040	0.055
L	2.87	3.12	0.113	0.123
M	1.65	2.13	0.065	0.084
N	15.49	16.26	0.610	0.640
O	13.50	14.50	0.531	0.571
P	16.50	17.50	0.650	0.689
Q	5.45 BSC		0.215 BSC	
R	2.00	2.75	0.079	0.108
S	7.10	7.50	0.280	0.295
Terminal 1	Gate			
Terminal 2	Drain			
Terminal 3	Source			
Terminal 4	Drain			



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